## CLAIMS

What is claimed is:

1. A memory subsystem comprising

two memory devices connected in parallel to a bus,

said bus including a plurality of bus lines for carrying substantially all address, data and control information needed by said memory devices,

said control information including device-select information,

said bus containing substantially fewer bus lines than the number of bits in a single address, and

said bus carrying device-select information without the need for separate device-select lines connected directly to individual memory devices.

2. The memory subsystem of claim 1 wherein said bus contains at least 8 bus lines adapted to carry at least 16 address bits and at least 8 data bits.

3. The memory subsystem of claim 1 wherein said bus also includes parallel lines for clock and power.

4. A system comprising

a memory subsystem of claim 1 wherein each bus of said memory subsystem is connected to its own transceiver device,

a transceiver bus connecting said transceiver devices, and

a means for transferring information between each of said buses of said memory subsystems and said transceiver bus, whereby memory subsystems may be integrated into a larger system having more memory than an individual memory subsystem.

5. The system of claim 4 having a plurality of memory subsystems.

6. The system of claim 4 further comprising a master device connected to said transceiver bus.

7. The system of claim 6 wherein said master device is selected from the group consisting of a central processing unit, a floating point unit and a direct memory access unit.

8. The system of claim 4 further comprising a peripheral device connected to the transceiver bus, said peripheral device adapted for connection to other devices not on the bus.

9. The system of claim 8 wherein said peripheral device is selected from the group consisting of an I/O interface port, a video controller and a disk controller.

10. The system of claim 5 wherein said transceiver bus is in a different plane than the plane of the bus of each of said memory subsystems.

11. The system of claim 5 wherein the bus of each memory subsystem lies substantially in a subsystem bus plane and said transceiver bus lies substantially in a plane orthogonal to said subsystem bus plane.

12. The system of claim 4 having at least two transceiver buses, each transceiver bus having a plurality of memory subsystem buses connected through a first transceiver to said transceiver bus,

each of said transceiver buses being further connected to a second transceiver adapted to interface to a second-order transceiver bus, whereby each transceiver bus is connected through said second transceiver to form a second-order transceiver bus unit.

13. A semiconductor subsystem bus for interconnecting semiconductor devices comprising

a plurality of semiconductor devices connected in parallel to a bus, at least one of said semiconductor

devices being a memory device or a transceiver device which in turn is connected to a memory subsystem,

said bus including a plurality of bus lines for carrying substantially all address, data and control information needed by said semiconductor devices,

said control information including semiconductor device-select information,

said bus containing substantially fewer bus lines than the number of bits in a single address, and

said bus carrying device-select information without the need for separate device-select lines connected directly to individual semiconductor devices, and

at least one modifiable register in each of the semiconductor devices on said bus, said modifiable registers being accessible from said bus, whereby the subsystem can be configured using signals transmitted on said bus.

14. The semiconductor subsystem bus of claim 13 wherein one type of modifiable register is an access-time register designed to store a time delay after which a device may take some specified action on said bus.

15. The semiconductor subsystem bus of claim 13 further comprising a semiconductor device having at least two access-time registers and

one of said access-time registers is permanently programmed to contain a fixed value and at least one of said access-time registers can be modified by information carried on said bus.

16. The semiconductor subsystem bus of claim 13 further comprising a memory device having at least one discrete memory section and also having a modifiable address register adapted to store memory address information which corresponds to each said discrete memory section.

17. The semiconductor subsystem bus of claim 16 wherein said memory address information comprises a pointer to said discrete memory section.

18. The semiconductor subsystem bus of claim 16 wherein said discrete memory section has a top and a bottom and said memory address information comprises pointers to said top and said bottom.

19. The semiconductor subsystem bus of claim 16 wherein said memory address information comprises

a pointer to said discrete memory section and

a range value indicating the size of said discrete memory section.

20. The semiconductor subsystem bus of claim 16 wherein said address registers of each of said discrete memory sections of each of said memory devices connected to said bus are set to contain memory address information that is different for each discrete memory section and such that the highest memory address in each discrete memory section is one less than the lowest memory address in another discrete memory section,

whereby memory may be organized into one or a small number of contiguous memory blocks.

21. The semiconductor subsystem bus of claim 16 further comprising a means for testing each of said discrete memory sections of each of said memory devices for proper function, and

for each non-functional discrete memory section, a means for setting at least one address register which corresponds to said discrete memory section to indicate that said discrete memory section is non-functional,

for each functional discrete memory section, a means for setting at least one address register which corresponds to said discrete memory section to contain such corresponding address information.

22. The semiconductor subsystem bus of claim 21 wherein said address registers corresponding to said discrete memory

sections are set to provide one contiguous memory block within the subsystem.

23. The semiconductor subsystem bus of claim 13 wherein one of said modifiable registers is a device identification register which can be modified to contain a value unique to that semiconductor device.

24. The semiconductor subsystem bus of claim 23 wherein said device identification register is set to contain a unique value which is a function of the physical position of that semiconductor device either along said bus or in relationship to other semiconductor devices or said bus.

25. A bus subsystem comprising

two semiconductor devices connected in parallel to a bus, wherein one of said semiconductor devices is a master device,

said master device including a means for initiating bus transactions,

said bus including a plurality of bus lines for carrying substantially all address, data and control information needed by said devices,

said control information including device-select information,

said bus containing substantially fewer lines than the number of bits in a single address, and

said bus carrying device-select information without the need for separate device-select lines connected directly to individual devices on said bus, whereby said master device initiates bus transactions which transfer information between said semiconductor devices on said bus.

26. The bus subsystem of claim 25 wherein one of said semiconductor devices is a memory device connected to said bus, said memory device having at least one discrete memory section and also having a modifiable address register adapted to store memory address information which corresponds to each said discrete memory section.

27. The bus subsystem of claim 26 wherein one of said semiconductor devices comprises a transceiver device connected in parallel to said bus and connected in parallel to a memory device on a bus other than said bus.

28. The bus subsystem of claim 26 further including a means for said master device to request said memory device to prepare for a bus transaction by sending a request packet along said bus, said memory device and said master device each having a device-internal means to prepare to begin said bus transaction during a

device-internal phase and further having a bus access means to effect said bus transaction during a bus access phase, said request packet including

a sequence of bytes containing address and control information,

said control information including information about the requested bus transaction and about the access time, which corresponds to a number of bus cycles, which needs to intervene before beginning said bus-access phase, and

said address information pointing to at least one memory location within one of said discrete memory sections of said memory device.

29. The bus subsystem of claim 28 wherein said memory device includes a means to read said control information and initiate said device-internal means at a time so as to complete said device-internal phase within said access time and begin said bus access phase after said number of bus cycles.

30. The bus subsystem of claim 28 wherein said control information comprises an op code.

31. The bus subsystem of claim 30 wherein said memory device includes sense amplifiers adapted to hold a bit of information or to precharge after a selected time and a means to

transfer a data block during a data block transfer either reading data from said memory device or writing data into said memory device, and

wherein said op code instructs said memory device to activate a response means, said response means including a means to

initiate a data block transfer,

select the size of said data block,

select the time to initiate said data block transfer,

access a control register, including reading from or writing to said control register,

precharge said sense amplifiers after each of said data block transfers is complete,

hold a bit of information in each of said sense amplifiers after each of said data block transfers is complete, or

select normal or page-mode access.

32. The bus subsystem of claim 31 wherein said data block transfer comprises a read from or a write to memory within a single memory device.

33. The bus subsystem of claim 28 further comprising a means for said master device to send control information to a specific one of said semiconductor devices on said bus by

including in said request packet a device identification number unique to said semiconductor device.

34. The bus subsystem of claim 28 further comprising a means for said master device to send control information to a selected one of said discrete memory portions by including in said request packet a specific memory address.

35. The bus subsystem of claim 28 further comprising a means for said master device to send control information to substantially all semiconductor devices on said bus by including in said request packet a special device identification number which is recognized by said semiconductor devices.

36. The bus subsystem of claim 28 wherein said control information specifies directly or indirectly the number of bus cycles for said master device and said memory device to wait before beginning said bus access phase.

37. The bus subsystem of claim 36 wherein, for a data block transfer, said master device and said memory device use the same access time and same data block size regardless of whether said data block transfer is a read or write operation.

38. The bus subsystem of claim 28 wherein said control information further includes a block-size value that encodes and specifies the size of the block of data to be transferred.

39. The bus subsystem of claim 38 wherein said block-size value is encoded as a linear value for relatively small block sizes values and is encoded as a logarithmic value for relatively larger block sizes.

40. The bus subsystem of claim 38 wherein said block-size value is encoded using four bits, and where the encoded value is

| Encoded Value | Block Size (Bytes) |
|---|---|
| 0 | 0 |
| 1 | 1 |
| 2 | 2 |
| 3 | 3 |
| 4 | 4 |
| 5 | 5 |
| 6 | 6 |
| 7 | 7 |
| 8 | 8 |
| 9 | 16 |
| 10 | 32 |
| 11 | 64 |
| 12 | 128 |
| 13 | 256 |
| 14 | 512 |
| 15 | 1024 |

41. The bus subsystem of claim 26 wherein said memory device is a DRAM device containing

a plurality of sense amplifiers,

a means to hold said sense amplifiers in an unmodified state after a read or write operation, leaving the device in page mode,

a means to precharge said sense amplifiers and

a means for selecting whether to precharge said sense amplifiers or to hold said sense amplifiers in an unmodified state.

42. The bus subsystem of claim 28 wherein said request packet comprises an even number of bytes.

43. The bus subsystem of claim 28 further including a means for generating and controlling a plurality of bus cycles, during which said bus carries said address, data and control information, and wherein alternate said bus cycles are designated odd cycles and even cycles, respectively, and wherein said request packet begins only on an even cycle.

44. The bus subsystem of claim 28 further including a means for generating ECC information corresponding to a block of data and a means for using said ECC information to correct errors in storing or reading said block of data, wherein said ECC information may be stored separately from said block of data.

45. The bus subsystem of claim 44 further comprising at least two of said memory devices wherein said ECC information and said corresponding block of data are stored in a first and a second said memory device, respectively, and said master device includes a means to write or read said block of data with error correction by sending separate ones of said request packets for said ECC information and for said corresponding block of data.

46. A bus subsystem comprising

a memory device and a master device connected in parallel on a bus,

a means for said master device to send a request packet and initiate a bus transaction and

a means for said master device to keep track of current and pending bus transactions,

said bus including a plurality of bus lines for carrying substantially all address, data and control information needed by said memory devices,

said bus containing substantially fewer lines than the number of bits in a single address, and

said bus carrying device-select information without the need for separate device-select lines connected directly to individual devices on said bus, whereby said master device initiates bus transactions which transfer information between devices on said bus and collisions on said bus are

avoided because said master device avoids initiating bus transactions which would conflict with current or pending bus transactions.

47. The bus subsystem of claim 46 having at least two of said master devices and including

a collision detecting means whereby a first said master device sending a first said request packet can detect a second said master device sending one of said colliding request packets, where one of said said colliding request packet may be sent simultaneous with the initial sending of or overlapping the sending of said first request packet, and

an arbitration means whereby said first and said second master devices select a priority order in which each of said master devices will be allowed to access said bus sequentially.

48. The bus subsystem of claim 47 wherein each of said master devices has a master ID number and each of said request packets includes a master ID position which is a predetermined number of bits in a predetermined position in said request packet, and wherein said collision detection means comprises

a means included in each master device for sending a request packet including said master ID number of said

master device in said master ID position of said request packet and

a means to detect a collision and invoke said arbitration means if any master device detects any other master ID number in said master ID position.

49. The bus subsystem of claim 47 wherein each of said master devices includes

a means for sending a request packet,

a means for driving a selected bus line or lines during at least one selected bus cycle while said request packet is being sent,

a means for monitoring said selected bus line or lines to see if a said master device is sending a colliding request packet and

a means for informing all other master devices that a collision has occurred and for invoking said arbitration means.

50. The bus subsystem of claim 47 wherein each of said master devices includes

a means, when sending a request packet, to drive a selected bus line or lines with a certain current during at least one selected bus cycle,

a means for monitoring said selected bus line or lines for a greater than normal current to see if another master device is driving that line or lines,

a means for detecting said greater than normal current, and

a means for informing all said master devices that a collision has occurred and for invoking said arbitration means.

51. The bus subsystem of claim 47 wherein said arbitration means comprises

a means for initiating an arbitration cycle,

a means for allocating a single bus line to each master device during at least one selected bus cycle relative to the start of said arbitration cycle,

a means for allocating each master device to a single bus line during one of said selected bus cycles if there are more master devices than available bus lines,

a means for each of said master devices which sent a colliding request packet to drive said bus line allocated to said master device during said selected bus cycle, and

a means in at least one of said master devices for storing information about which master devices sent a colliding request packet,

whereby said master devices can monitor selected bus lines during said arbitration cycle and identify each said master device which sent a colliding request packet.

52. The bus subsystem of claim 47 wherein said arbitration means comprises

a means included in a first one of said master devices which sent colliding request packets for identifying each of said master devices which sent colliding request packets,

a means for assigning a priority to each said master device which sent a colliding request packet, and

a means for allowing each said master device which sent a colliding request packet to access the bus sequentially according to that priority.

53. The bus subsystem of claim 52 wherein said priority is based on the physical location of each of said master devices.

54. The bus subsystem of claim 52 wherein said priority is based on said master ID number of said master devices.

55. The bus subsystem of claim 52 wherein each of said master devices includes a means, when sending a colliding request packet, for deciding which master device can send the next request packet in what order or at what time, whereby no master

device may send a new request packet until responses to each pending request packet have been completed or scheduled.

56. A bus subsystem comprising

a plurality of semiconductor devices connected in parallel to a bus,

said bus including a plurality of bus lines for carrying substantially all address, data and control information needed by said semiconductor devices,

said control information including device-select information,

said bus containing substantially fewer lines than the number of bits in a single address,

said bus carrying said device-select information without the need for separate device-select lines connected directly to individual semiconductor devices,

said semiconductor devices including a reset means having an input and an output, the output of the reset means of one semiconductor device being connected to the input of the reset means of the next semiconductor device in series.

57. The bus subsystem of claim 56 further including system reset means comprising

a means for generating a first and a second reset signal,

a means for passing said first reset signal to a first of said semiconductor devices and then to subsequent ones of said semiconductor devices in series and

a means for passing a second reset signal to said first semiconductor device and then to said subsequent semiconductor devices in series,

said bus subsystem including one of said semiconductor devices containing

a device identification register adapted to contain a number unique to said semiconductor device within said bus subsystem,

a device identification register setting means, and

a device reset means for resetting said semiconductor device to some desired, known reset state in response to said first reset signal and for setting said device identification register in response to said second reset signal,

whereby said bus subsystem can be reset to a known reset state with a unique device identification value in said device identification register of each of said semiconductor devices.

58. The bus subsystem of claim 57 wherein said desired, known reset state is where all registers in the semiconductor device are cleared and the state machines are reset.

59. The bus subsystem of claim 57 wherein said device identification register setting means comprises

a means for detecting said second reset signal,

a means for reading a device identification number from said bus lines at a specific time relative to said second reset signal and

a means for storing said device identification number in said device identification register of said semiconductor device.

60. The bus subsystem of claim 57 wherein said second reset signal comprises multiple pulse sequences and wherein said device identification setting means includes

a means for interpreting said pulse sequences as a device identification number and

a means for storing said device identification number in said device identification register of said semiconductor device.

61. The bus subsystem of claim 57 wherein said device reset means comprises an n-stage shift register capable of storing n-bit values, wherein said device reset means interprets a specific value in said shift register as said first reset signal and

interprets a specific value in said shift register as said second reset signal.

62. The bus subsystem of claim 57 wherein one of said semiconductor devices is a master device, said master device including a means for generating said first and said second reset signals.

63. The bus subsystem of claim 57 wherein one of said semiconductor devices is a master device, said master device including

a master ID register,

a means for assigning a master ID number to said master device and

a means for storing said master ID number in said master ID register.

64. The bus subsystem of claim 63 further comprising a second one of said master devices, and a means for a first one of said master devices to assign a master ID number to substantially all other said master devices, whereby said first master device assigns one of said master ID numbers to each of said master devices on said bus subsystem and each said master device stores said assigned master ID number in said master ID register.

65. The bus subsystem of claim 57 wherein one of said semiconductor devices includes a device-type register adapted to contain an identifier characteristic of that type of semiconductor device, and one or more modifiable registers, at least one of which is an access-time register adapted for storing access times.

66. The bus subsystem of claim 65 wherein one of said semiconductor devices is a master device having

a means for selecting a semiconductor device,

a means for reading said device-type register of said selected semiconductor device,

a means for determining the device type of said selected semiconductor device,

a means for determining access-time values appropriate for said selected semiconductor device and for storing said access-time values in said access-time registers of said selected semiconductor device, and

a means for selecting and storing other values appropriate for said selected semiconductor device in corresponding registers of said selected semiconductor device,

whereby said master device can select a semiconductor device, determine what type it is, and set said access-time and other registers to contain appropriate values.

67. The bus subsystem of claim 66 further comprising a memory device having at least one discrete memory section and at least one modifiable address register adapted to store memory address information which corresponds to each of said discrete memory sections, and

said master device further comprising a means for selecting and testing each of said discrete memory sections and a means for storing address information in said address registers corresponding to each of said discrete memory sections, whereby said master device can test all said discrete memory sections and assign unique address values thereto.

68. A bus subsystem comprising

two semiconductor devices connected in parallel to a bus, one of said semiconductor devices being a master device,

said bus including a plurality of bus data lines for carrying substantially all address, data and control information needed by said semiconductor devices,

said control information including device-select information,

said bus containing substantially fewer of said bus data lines than the number of bits in a single address, and

said bus carrying device-select information without the need for separate device-select lines connected directly to individual semiconductor devices,

wherein all of said bus data lines are terminated transmission lines and all of said address, data and control information is carried on said bus data lines as a sequential series of bits in the form of low-voltage-swing signals.

69. The bus subsystem of claim 68 further comprising a semiconductor device including a current-mode driver connected to drive one of said bus data lines.

70. The bus subsystem of claim 69 further comprising a semiconductor device having a means to measure the voltage of said low-voltage-swing signals on a selected one of said bus data lines, whereby said semiconductor device can determine whether zero, one, or more than one of said current-mode drivers are driving said selected bus data line.

71. The bus subsystem of claim 70 further comprising a semiconductor device having

a plurality of input receivers connected to one of said bus data lines, and

a selection means for selecting said input receivers one by one to sense and store, one at a time, the bits of said sequential series of bits.

72. The bus subsystem of claim 70 further comprising a semiconductor device having two input receivers connected to one of said bus data lines.

73. A bus subsystem comprising

two semiconductor devices connected in parallel to a bus having a first and a second end, said bus including a bus clock line, said bus clock line having first and second ends corresponding to said first and second ends of said bus, respectively,

a clock generator connected to said first end of said bus clock line to generate early bus clock signals with a normal rise time, and

signal return means at said second end of said bus clock line to return said early bus clock signals to said first end of said bus as corresponding late bus clock signals,

whereby each of said early bus clock signals will propagate from said clock generator along said clock line starting from said first end to said second end of said bus and then return at a later time to said first end of said

bus as a corresponding late bus clock signal, whereby each semiconductor device on said bus can detect said early bus clock signals and said corresponding late bus clock signals.

74. The bus subsystem of claim 73 further comprising a first and a second said bus clock line having first and second ends at said first and said second ends of said bus, respectively, wherein said signal return means directly connects said second ends of said first and said second bus clock lines whereby each of said early bus clock signals will propagate from said clock generator at said first end of said bus along said first bus clock line to said second end of said bus and then return on said second bus clock line to said first end of said bus as one of said corresponding late bus clock signals.

75. The bus subsystem of claim 73 wherein said signal return means comprises said first bus clock line without a line terminator at said second end thereof whereby each of said early bus clock signals reaching said second end of said first bus clock line will be reflected back along said first bus clock line as said corresponding late bus clock signals.

76. The bus subsystem of claim 73 further comprising

a means for operating said bus in bus cycles timed to have a certain bus cycle frequency and a corresponding bus cycle period and

a means for operating said clock generator with a period of twice the bus cycle period.

77. The bus subsystem of claim 76 wherein said bus cycle frequency is greater than approximately 50 MHz and less than or equal to approximately 500 MHz.

78. The bus subsystem of claim 73 further including a semiconductor device having an internal device clock generating means to derive the midpoint time between said early and corresponding late bus clock signals and to generate an internal device clock synchronized to said midpoint time.

79. The bus subsystem of claim 73 further including a semiconductor device having a low-skew clock generator circuit comprising

a first delay line having an input, an output and a basic delay and means for synchronizing the output of said first delay line with said early bus clock signal,

a second delay line having said basic delay plus a variable delay, said second delay line having an output and

a means for synchronizing the output of said second delay line with said late bus clock signal, and

a third delay line having a third delay and a means to set said third delay midway between the delays of said first and second delay lines, said third delay line having an output which provides an internal device clock signal synchronized to a time halfway between said early and said late bus clock signals.

80. The bus subsystem of claim 73 wherein said early and said late bus clock signals are low-voltage-swing signals that transition cyclically between low and high logical values, and further including a semiconductor device having a low-skew clock generator circuit comprising

a DC amplifier to convert said early and said late bus clock signals into full-swing logic signals,

a first variable delay line having a first variable delay and an input and an output, the input of said first variable delay line being connected to said DC amplifier

a first, a second and a third additional delay line, each having an input and an output, the input of each of said additional delay lines being connected to the output of said first delay line,

said first additional delay line having a fixed delay,

said second additional delay line having said fixed delay plus a second variable delay, and

said third additional delay line having said fixed delay plus one half of said second variable delay,

a first clocked input receiver connected to sample said early bus clock signal and gated by said output of said first additional delay line,

a means for adjusting said first variable delay so said first clocked input receiver samples said early bus clock signal just as said early bus clock signal transitions,

a second clocked input receiver connected to sample said late bus clock signal and gated by said output of said second additional delay line,

a means for adjusting said second variable delay so said second clocked input receiver samples said late bus clock signal just as said late bus clock signal transitions,

whereby said output of said third additional delay line is synchronized to a time halfway between said outputs of said first and said second additional delay lines, and said output of said third additional delay line provides an internal device clock signal.

81. The bus subsystem of claim 80 further comprising a semiconductor device having

a first one of said low-skew clock generator circuits which generates a "true" internal device clock signal and

a second one of said low-skew clock generator circuits connected to generate a "complement" internal device clock signal synchronized with but opposite in logical value to said "true" internal device clock signal.

82. A DRAM device designed to be connected to an external bus having a plurality of bus lines for carrying substantially all address, data and control information needed by said DRAM device as a sequential series of bits, said control information including device-select information, said external bus containing substantially fewer said bus lines than the number of bits in a single address, and said bus carrying device-select information without the need for separate device-select lines connected directly to said DRAM device, said DRAM device comprising

an array of memory cells connected in rows and columns, each of said memory cells adapted to store one of said bits,

a row address selection means for selecting one of said rows,

a column sense amp connected to each of said columns, each of said column sense amps adapted to latch one of said

bits as a binary logical value or to precharge to a selected state,

a column decoding means connected to each of said column sense amps for selecting a plurality of said column sense amps for inputting one of said bits to or outputting one of said bits from said memory cells,

an internal I/O bus having a plurality of internal I/O lines wherein each of said internal I/O lines is connected to a plurality of said column sense amps, and

a plurality of bus connection means designed to connect said internal I/O lines to said external bus,

whereby a selected bit of said sequential series of bits can be transferred from said external bus to a selected one of said memory cells or said bit contained in a selected one of said memory cells can be transferred to said external bus.

83. The DRAM device of claim 82 further comprising

an output driver connected to one said bus connection means,

an output multiplexer having an output connected to said output driver and a plurality of inputs, each of said inputs being connected to one of said internal I/O lines, and

a control means to select whether said output driver can drive said external bus,

whereby a plurality of memory cells are selected using said row address selection means and said column decoding means and a plurality of bits contained in said plurality of memory cells are output through said column sense amps to said internal I/O bus to said output multiplexer to said output driver to said external bus.

84. The DRAM device of claim 82 further comprising

a plurality of input receivers connected to one of said bus data lines and to said internal I/O bus,

a selection means for selecting said input receivers one by one to sense and store, one at a time, the bits of said sequential series of bits, and

a control means to select whether an input receiver can drive said internal I/O bus, whereby a bit of said sequential series of bits is input from said external bus through one of said input receivers to one of said internal I/O lines to one of said column sense amps to one of said memory cells.

85. The DRAM device of claim 82 further comprising

a first and a second half-array of said memory cells wherein each said row of said array of said memory cells is subdivided into two parts,

a first and a second one of said internal I/O buses connected to said column sense amps in said first and said second half-arrays, respectively, and

a column decoder means to gate selected ones of said column sense amps connected to said memory cells in a selected row of said first and said second half-arrays simultaneously.

86. The DRAM device of claim 85 wherein said column decoder means selects sixteen column sense amps at a time.

87. The DRAM device of claim 82 wherein said external bus operates at a certain speed and wherein said DRAM device includes four of said internal I/O buses, each of which operates at one-fourth the speed of said external bus.

88. The DRAM device of claim 82 further comprising

a means for precharging one of said column sense amps to a precharged state from which a binary logical value can quickly be loaded into said column sense amp,

if said column sense amp contains a binary logical value, a means for latching the logical value currently contained in said column sense amp and

a means for instructing said DRAM device to precharge said column sense amp or latch said binary logical value in said column sense amp.

89. The DRAM device of claim 88 further comprising a means for instructing said DRAM device to precharge said column sense amp without further instruction whenever said row address selection means selects a different one of said rows.

90. The DRAM device of claim 88 further comprising a means for instructing said DRAM device to precharge said column sense amp without further instruction at a first or a second preselected time after latching the latest said binary logical value, said first preselected time being long enough for said DRAM to latch said binary logical value into said column sense amp and transfer said binary logical value into memory or onto one of said internal I/O lines, and said second preselected time being a variable which can be stored in said DRAM device whereby said DRAM can latch a binary logical value into said column sense amp for transferring said binary logical value into or out of a selected said memory cell, then precharge to allow a faster subsequent read or write.

91. A package containing

a semiconductor die having a side, circuitry and a plurality of connecting areas positioned along or near said side, spaced at a selected pitch and connected to said circuitry,

said package comprising a plurality of bus connecting means for connecting to a plurality of external bus lines, each of said external bus lines corresponding to one of said connecting areas, each of said bus connecting means being

positioned on a first side of said package,

connected to one said external bus line and to said corresponding connecting area on said semiconductor die, and

spaced at a pitch substantially identical to said selected pitch of said connecting areas,

whereby each of said external bus lines can be connected to said corresponding connecting area on said semiconductor die by bus connection means positioned along a single side of said package.

92. The package of claim 91 further comprising a plurality of said bus connecting means wherein each of said bus connecting means includes

a pin adapted for connection to one of said external bus lines and

a wire connecting said pin to one of said connecting areas on said semiconductor die,

said wire having an effective lead length less than about 4 millimeters and wherein the effective lead length of said wire of each of said bus connection means for said package is approximately equal.

93. A plurality of packages of claim 91 wherein at least two of said semiconductor die are memory devices, each of said packages being generally flat, having a top and a bottom, and wherein

said packages are physically secured adjacent and parallel to each other in a stack,

where a first one of said packages is adjacent to a second one of said packages in said stack, said top of said first package is substantially aligned with said bottom of said second package, and

said bus connecting means of each of said packages are substantially aligned and are lying substantially in a plane.

94. The plurality of packages of claim 93 further comprising a plurality of stacks wherein each of said bus connecting means can be electrically connected to corresponding said bus connecting means in each of said stacks.

95. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus, and

at least one modifiable identification register accessible to said bus through said connection means, whereby data may be transmitted to said register via said bus and enable said device thereafter to be uniquely identified.

96. The semiconductor device of claim 95 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

97. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus, and

at least one modifiable register to hold device address information, said modifiable register accessible to said bus through said connection means, whereby data may be transmitted to said register via said bus which enables said device thereafter to respond to a predetermined range of addresses.

98. The semiconductor device of claim 97 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives

substantially all address, data and control information over said bus.

99. The semiconductor device of claim 98 wherein said memory device has at least one discrete memory section and also has at least one modifiable address register adapted to store memory address information which corresponds to each said discrete memory section.

100. The semiconductor device of claim 99 wherein said memory address information comprises a pointer to said discrete memory section.

101. The semiconductor device of claim 100 wherein said discrete memory section has a top and a bottom and said memory address information comprises pointers to said top and said bottom.

102. The semiconductor device of claim 100 wherein said memory address information comprises

a pointer to said discrete memory section and

a range value indicating the size of said discrete memory section.

103. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data and control information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus, and

at least one modifiable access-time register accessible to said bus through said connection means, whereby data may be transmitted to said register via said bus which establishes a predetermined amount of time that said semiconductor device thereafter must wait before using said bus in response to a request.

104. The semiconductor device of claim 103 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

105. The semiconductor device of claim 103 further comprising at least two access-time registers and one of said access-time registers is permanently programmed to contain a fixed value and at least one of said access-time registers can be modified by information carried on said bus.

106. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, and wherein each said bus line is a terminated transmission line, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus, and

a bus line driver capable of producing a low-voltage-swing signal on one of said terminated transmission lines.

107. The semiconductor device of claim 106 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

108. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said bus further including at least one bus clock line for carrying early and late bus clock signals, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus, and

an internal device clock generating means which generates an internal device clock synchronized to a time halfway between said early and said late bus clock signals.

109. The semiconductor device of claim 108 wherein said bus further includes a first and a second one of said bus clock lines, said first bus clock line carries said early bus clock signal and said second bus clock line carries said late bus clock signal, said semiconductor device further comprising a means to detect said early bus clock signal on said first bus clock line and a means to detect said late bus clock signal on said second bus clock line.

110. The semiconductor device of claim 109 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

111. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying as a sequential series of bits substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a

separate device-select line connect d directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus,

a plurality of input receivers connected to one of said bus data lines and

a selection means for selecting said input receivers one by one to sense and store, one at a time, the bits of said sequential series of bits.

112. The semiconductor device of claim 111 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

113. The semiconductor device of claim 112 wherein two input receivers are connected to one of said bus lines.

114. A semiconductor device capable of use in an architecture for a semiconductor system bus including a plurality of semiconductor devices connected in parallel to a bus wherein said bus system includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication

with substantially every other semiconductor device connected to said system bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said system bus,

an internal input/output bus within said semiconductor device having more lines than said system bus, and

a means for multiplexing the lines of said internal bus to the lines of said system bus, whereby said system bus can run at a higher speed than said internal bus.

115. The semiconductor device of claim 114 wherein said semiconductor device is a memory device which connects substantially only to said system bus and sends and receives substantially all address, data and control information over said system bus.

116. A semiconductor device capable of use in an architecture for a semiconductor system bus including a plurality of semiconductor devices connected in parallel to a bus wherein said system bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select

information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said system bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said system bus,

an internal input/output bus within said semiconductor device having more lines than said system bus,

a means for multiplexing the lines of said internal bus to the lines of said system bus, whereby said system bus can run at a higher speed than said internal bus, and

at least one modifiable identification register accessible to said system bus through said connection means, whereby data may be transmitted to said register via said system bus and which enables said device thereafter to be uniquely identified.

117. The semiconductor device of claim 116 wherein said semiconductor device is a memory device which connects substantially only to said system bus and sends and receives substantially all address, data and control information over said system bus.

118. A semiconductor device capable of use in an architecture for a semiconductor system bus including a plurality of semiconductor devices connected in parallel to a bus wherein said system bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said system bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said system bus,

an internal input/output bus within said semiconductor device having more lines than said system bus,

a means for multiplexing the lines of said internal bus to the lines of said system bus, whereby said system bus can run at a higher speed than said internal bus, and

at least one modifiable register to hold device address information, said modifiable register accessible to said system bus through said connection means, whereby data may be transmitted to said register via said system bus which enables said device thereafter to respond to a predetermined range of addresses.

119. The semiconductor device of claim 118 wherein said semiconductor device is a memory device which connects substantially only to said system bus and sends and receives substantially all address, data and control information over said system bus.

120. The semiconductor device of claim 119 wherein said memory device has at least one discrete memory section and also has at least one modifiable address register adapted to store memory address information which corresponds to each said discrete memory section.

121. A semiconductor device capable of use in an architecture for a semiconductor system bus including a plurality of semiconductor devices connected in parallel to a bus wherein said system bus includes a plurality of bus lines for carrying substantially all address, data and control information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said system bus, and has substantially fewer bus lines than the number of bits in a single address, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said system bus,

an internal input/output bus within said semiconductor device having more lines than said system bus,

a means for multiplexing the lines of said internal bus to the lines of said system bus, whereby said system bus can run at a higher speed than said internal bus, and

at least one modifiable access-time register accessible to said system bus through said connection means, whereby data may be transmitted to said register via said system bus which establishes a predetermined amount of time that said semiconductor device thereafter must wait before using said system bus in response to a request.

122. The semiconductor device of claim 121 wherein said semiconductor device is a memory device which connects substantially only to said system bus and sends and receives substantially all address, data and control information over said system bus.

123. The semiconductor device of claim 121 further comprising at least two access-time registers and one of said access-time registers is permanently programmed to contain a fixed value and at least one of said access-time registers can be modified by information carried on said system bus.

124. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes

a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, wherein said address, data, control and device-select information is carried over said bus in the form of request packets and bus transactions, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus,

a means to receive said request packets over said bus,

a means to decode information in said request packets, and

a means to respond to said information in said request packets.

125. The semiconductor device of claim 124 wherein said means to decode information in said request packet further comprises

a means to identify and decode said control information in said request packet,

a means to identify and decode said device-select information in said request packet,

a means to identify and decode said address information in said request packet and

a means to determine whether said control information or said address information instructs said semiconductor device to begin a response.

126. The semiconductor device of claim 124 wherein each of said bus transactions is carried out in response to said address and said control information in one of said request packets, and wherein said means to identify and decode information in said request packets includes a means to identify a sequence of bytes on said bus as one of said request packets containing said address and said control information, said control information including information about the type of said bus transaction being requested and the access time which needs to intervene before beginning said bus transaction over said bus and said address and said control information includes device-select information instructing one or more said semiconductor devices to respond to said address and said control information.

127. The semiconductor device of claim 124 further comprising

a plurality of sense amplifiers adapted to precharge to a selected state or to latch a bit of information,

a means to hold said sense amplifiers in an unmodified state after latching one of said bits of information,

a means to precharge said sense amplifiers and

a means for selecting whether said semiconductor device should precharge said sense amplifiers or should hold said sense amplifiers in an unmodified state.

128. The semiconductor device of claim 124 wherein said means to respond to said information, where said information is control information, further comprises a means to

transfer a data block during a data block transfer, further including a means to

read data from said semiconductor device and

write data into said semiconductor device, and

initiate a data block transfer,

transfer a data block of a selected size,

transfer a data block at a selected time,

access a control register, including a means to read from or write to said control register, or

select normal or page-mode access.

129. The semiconductor device of claim 124 further comprising a means to respond to said information in said request

packet if said information includes a device identification number unique to said semiconductor device.

130. The semiconductor device of claim 124 further comprising a means to respond to said information in said request packet if said information includes a special device identification number which calls for said semiconductor device to respond.

131. The semiconductor device of claim 124 further comprising a means to respond to said information in said request packet if said information includes an address unique to said semiconductor device.

132. The semiconductor device of claim 124 further comprising a means to interpret said control information and decode the time to wait before beginning said bus transaction over said bus.

133. The semiconductor device of claim 124 further comprising a means to interpret said control information and decode the size of a data block to transfer during one of said bus transactions.

134. The semiconductor device of claim 124, 125, 126, 127, 128, 129, 130, 131, 132 or 133 wherein said semiconductor device is a memory device which connects substantially only to said bus and sends and receives substantially all address, data and control information over said bus.

135. A semiconductor device capable of use in a semiconductor bus architecture including a plurality of semiconductor devices connected in parallel to a bus wherein said bus includes a plurality of bus lines for carrying substantially all address, data, control and device-select information needed by said semiconductor device for communication with substantially every other semiconductor device connected to said bus, and has substantially fewer bus lines than the number of bits in a single address, and carries device-select information for said semiconductor device without the need for a separate device-select line connected directly to said individual semiconductor device, wherein said address, data, control and device-select information is carried over said bus in the form of request packets and bus transactions, said semiconductor device comprising

connection means adapted to connect said semiconductor device to said bus,

a means to encode address and control information in said request packets and

a means to send said request packets over said bus.

136. The semiconductor device of claim 135 further comprising a means to request a bus transaction wherein each of said bus transactions is carried out in response to said address and said control information in one of said request packets, and wherein said means to encode information in said request packets includes a means to mark a sequence of bytes on said bus as one of said request packets, said control information including information about the type of said bus transaction being requested and the access time which needs to intervene before beginning said bus transaction over said bus and said address and said control information includes device-select information instructing one or more said semiconductor devices to respond to said address and said control information.

137. The semiconductor device of claim 135 wherein one or more of said plurality of semiconductor devices has a unique device identification number, said semiconductor device further comprising a means to send control information to a specific one of said plurality of semiconductor devices by including in said request packet a selected said device identification number.

138. The semiconductor device of claim 135 wherein each of said plurality of semiconductor devices is adapted to respond to

a special device identification number, said semiconductor device further comprising a means to send control information to each of said plurality of semiconductor devices by including in said request packet said special device identification number.

139. The semiconductor device of claim 135 wherein one or more of said plurality of semiconductor devices is a memory device having a plurality of addresses, said semiconductor device further comprising a means to send control information to a specific address or range of addresses in one of said plurality of semiconductor devices by including said specific address or range of addresses in said request packet.

140. The semiconductor device of claim 135 wherein at least one of said request packets is a request packet requesting a bus transaction which is followed by a corresponding one of said bus transactions, said semiconductor device further comprising a means to encode said control information to specify directly or indirectly the time between the end of said request packet requesting a bus transaction and said corresponding bus transaction over said bus.

141. The semiconductor device of claim 140 wherein one type of said bus transactions is a transfer of a data block, said semiconductor device further comprising a means to encode said

control information to specify the size of said data block to transfer.

142. The semiconductor device of claim 140 further comprising a means to keep track of current and pending bus transactions, whereby collisions on said bus are avoided because said semiconductor device avoids initiating bus transactions which would conflict with current or pending bus transactions.

143. The semiconductor device of claim 135 wherein said semiconductor device is a first master device and one of said plurality of semiconductor devices is a second master device, further comprising

a collision detecting means whereby said first master device when sending a first one of said request packets can detect said second master device sending a colliding one of said request packets, where said colliding request packet may be sent simultaneous with the initial sending of or overlapping the sending of said first request packet, and

an arbitration means whereby said first and said second master devices select a priority order in which each of said master devices will be allowed to access said bus sequentially.

144. The semiconductor device of claim 143 wherein said semiconductor device is a master device and at least one of said plurality of semiconductor devices is a master device, each of said master devices has a master ID number and each of said request packets includes a master ID position which is a predetermined number of bits in a predetermined position in said request packet, and wherein said collision detection means comprises

a means for said semiconductor device to send its master ID number in said request packet and

a means to detect a collision and invoke said arbitration means if said semiconductor device detects any other master ID number in said master ID position.

145. The semiconductor device of claim 144 wherein said system bus architecture includes a means for carrying information on said bus during bus cycles, said semiconductor device further comprising

a means for driving a selected bus line or lines during at least one selected bus cycle while sending each said request packet,

a means for monitoring said selected bus line or lines to see if another said master device is sending one of said colliding request packets and

a means for informing all said master devices that a collision has occurred and for invoking said arbitration means.

146. The semiconductor device of claim 145 further comprising

a means, when sending a request packet, for driving a selected bus line or lines with a certain current during at least one selected bus cycle,

a means for monitoring said selected bus line or lines for a greater than normal current to see if another said master device is driving that line or lines,

a means for detecting said greater than normal current, and

a means for informing all said master devices that a collision has occurred and for invoking said arbitration means.

147. The semiconductor device of claim 143 wherein said arbitration means comprises

a means for initiating an arbitration cycle,

a means for allocating a single bus line to each said master device during at least one selected bus cycle relative to the start of said arbitration cycle,

a means for allocating each said master device to a single bus line during one of said selected bus cycles if there are more master devices than available bus lines,

a means for each of said master devices which sent one of said colliding request packets to drive said bus line allocated to said master device during said selected bus cycle, and

a means in at least one of said master devices for storing information about which master devices sent one of said colliding request packets,

whereby said master devices can monitor selected bus lines during said arbitration cycle and identify each said master device which sent one of said colliding request packets.

148. The semiconductor device of claim 143 wherein said arbitration means comprises

a means for identifying each of said master devices which sent one of said colliding request packets,

a means for assigning a priority to each said master device which sent one of said colliding request packets, and

a means for allowing each said master device which sent one of said colliding request packets to access the bus sequentially according to that priority.

149. The semiconductor device of claim 143 wher in said priority is based on the physical location of each of said master devices.

150. The semiconductor device of claim 143 wherein said priority is based on said master ID number of said master devices.